

Data sheet acquired from Harris Semiconductor CHS098A - Revised March 2002

CD40107B Types

CMOS Dual 2-Input NAND Buffer/Driver

High-Voltage Type (20-Volt Rating)

The CD40107B is a dual 2-input NAND buffer/driver containing two independent 2-input NAND buffers with open-drain single n-channel transistor outputs. This device features a wired-OR capability and high output sink current capability (136 mA typ. at $V_{\mbox{DD}}$ = 10 V, $V_{\mbox{DS}}$ = 1 V). The CD40107B is supplied in the 8-lead dual-in-line plastic (Mini-DIP) package (E suffix), 8-lead small-outline package (NSR suffix), 14-lead hermetic frit-seal ceramic package (F suffix), and in chip form (H suffix).

Features:

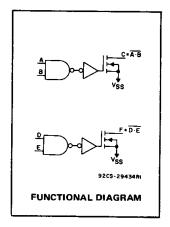
- 32 times standard B-Series output current drive sinking capability — 136 mA typ. @ VDD = 10 V, VDS = 1 V
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μ A at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings
- Noise margin, full package temperature range, RL to $V_{DD} = 10 \text{ k}\Omega$:

1 V at V_{DD} = 5 V

2 V at V_{DD} = 10 V

2.5 V at V_{DD} ≃ 15 V

■ Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"



Applications

- Driving relays, lamps, LEDs
- Line driver
- Level shifter (up or down)

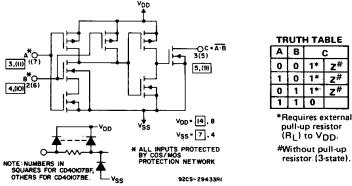


Fig. 1 — Schematic diagram of CD40107B (one of 2 gates)

DRAIN-TO-SOURCE VOLTAGE (VDS) -V 92CS-29444RI

Fig.2 - Typical output low (sink) current characteristics.

MAXIMUM RATINGS, Absolute-Maximum Values: DC SUPPLY-VOLTAGE RANGE, (VDD)



For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

LIN		
MIN.	MAX.	UNITS
3	18	٧

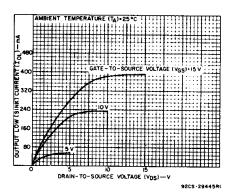


Fig.3 - Minimum output low (sink) current characteristics.

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CD40107B Types

DYNAMIC ELECTRICAL CHARACTERISTICS at TA = 25°C, CL = 50 pF, Input t, tf = 20 ns

	TEST CONDIT	LIMITS			
CHARACTERISTIC		V _{DD} Volts	Typ.	Max.	UNITS
Propagation Delay:	RL* = 120 Ω	5	100	200	
High-to-Low, tpHL		10	45	90	ns
		15	30	60	1
Low-to-High, tpLH	R _L * = 120 Ω	5	100	200	
		10	60	120	ns
		15	50	100	1
Transition Time:	RL* = 120 Ω	5	50	100	
High-to-Low, t _{THL}		10	20	40	ns
High-to-cow, tTHL		15	10	20	
Low-to-High, t _{TLH}	RL* = 120 Ω	5	50	100	
		10	35	70	ns
		15	25	50	1
Average Input Capacitance, CIN	Any Input		5	7.5	pF
Average Output Capacitance, COUT	Any Output		30	_	pF

^{*} R_L is external pull-up resistor to V_{DD}.

STATIC ELECTRICAL CHARACTERISTICS

CHARACTER-	CON	DITIO	NS	LIMIT	S AT I	NDICA	ATED T	EMPEF	RATURE	s (°C)	UNITS
ISTIC	Vο	VIN	V_{DD}						+25		0.0
	(V)	(V)	(V)	-55	–40	+85	+125	Min.	Тур.	Max.	
Quiescent Device Current IDD Max.	.	0,5	5	1	1	30	30	-	0.02	1	
		0,10	10	2	2	60	60	1	0.02	2	μΑ
		0,15	15	4	4	120	120		0.02	4	
	_	0,20	20	20	20	600	600	_	0.04	20	
Output Low	0.4	0,5	5	21	20	14	12	16	32	_	
(Sink) Current	1	0,5	5	44	42	30	25	34	68	_	
	0.5	0,10	10	49	46	32	28	37	74	_	
	1	0,10	10	89	85	60	51	68	136		mA
	0.5	0,15	15	66	63	44	38	50	100	-	'''C
Output High (Source) Current IOH Min.	No Internal Pull-Up Device										
Input Low	4.5	_	5		1	.5		-	_	1.5	
Voltage	9		10			3		_	_	3	
VIL Max.*	13.5	_	15			1		-	_	4	
Input High Voltage VIH Min.*	0.5,4.5	_	5		3	.5		3.5	_	_	٧
	1,9	_	10			7		7	-	_]]
	1.5,13.5	-	15	11			11	-	-		
Input Current		0,18	18	±0.1	±0.1	±1	±1	-	±10 ⁻⁵	±0.1	μΑ
Output Leakage Current IOZ Max.	18	0,18	18	2	2	20	20	_	10-4	2	μА

^{*} Measured with external pull-up resistor, $R_L = 10 \text{ k}\Omega$ to V_{DD} .

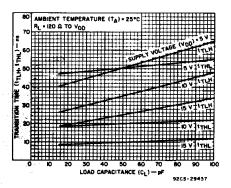


Fig.4 — Typical transition time as a function of load capacitance.

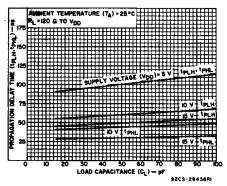


Fig.5 — Typical propagation delay time as a function of load capacitance.

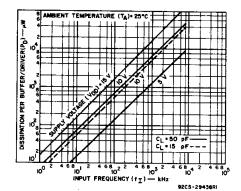


Fig.6 - Typical power dissipation as a function of input frequency.

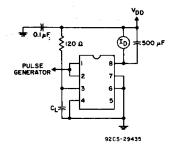
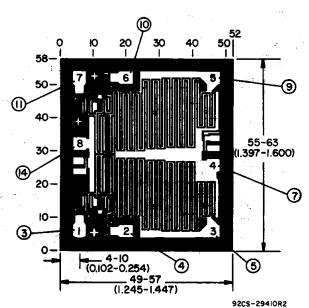


Fig. 7 – Power-dissipation test circuit for CD40107BE.

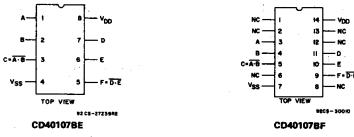
CD40107B Types



NOTE: NOS. IN PADS FOR CD40107BE NOS. OUTSIDE CHIP FOR CD40107BF

Dimensions and Pad Layout for CD40107BH.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10⁻³ inch).



TERMINAL ASSIGNMENTS

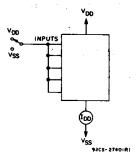


Fig.8 — Quiescent-device current test circuit.

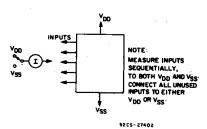


Fig. 9 - Input-current test circuit.

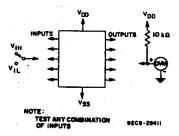


Fig.10 — Input-voltage test circuit.

Special Considerations for CD40107B

1. Limiting Capacitive Currents for CL > 500 pF, $\rm V_{DD}\!>$ 15 V.

For VDD > 15 V, and load capacitance (CL) from output to ground > 500 pF, an external 25 Ω series limiting resistor should be inserted between the output terminal and CL. No external resistor is necessary if CL < 500 pF or VDD < 15 V.

2. Driving Inductive Loads

When using the CD40107B to drive inductive loads, the load should be shunted with a diode to prevent high voltages from developing across the CD40107B output.

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